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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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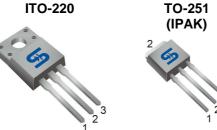


600V, 11A, 0.38Ω N-Channel Power MOSFET





**ITO-220** 



Pin Definition: 1. Gate

- 2. Drain
- 3. Source

#### **Key Parameter Performance**

Parameter	Value	Unit
$V_{DS}$	600	٧
R <sub>DS(on)</sub> (max)	0.38	Ω
$Q_g$	20.5	nC

#### TO-252 (DPAK)



#### **Features**

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

#### **Application**

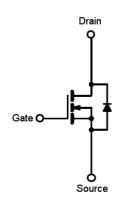
- Power Supply.
- Lighting

### **Ordering Information**

Part No.	Package	Packing
TSM60N380CI C0G	ITO-220	50pcs / Tube
TSM60N380CH C5G	TO-251	75pcs / Tube
TSM60N380CP ROG	TO-252	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Ratings** (T<sub>A</sub>=25°C unless otherwise noted)

Doromotor	Cumbal	Limit		11
Parameter	Symbol	ITO-220	IPAK/DPAK	Unit
Drain-Source Voltage	V <sub>DS</sub>		600	V
Gate-Source Voltage	$V_{GS}$	±30		V
Continuous Drain Current (Note 1) $T_C = 25^{\circ}C$	I <sub>D</sub>		11	Α
Pulsed Drain Current (Note 2)	I <sub>DM</sub>		33	Α
Total Power Dissipation @ T <sub>C</sub> =25°C	P <sub>DTOT</sub>	33	125	W
Single Pulsed Avalanche Energy (Note 3)	E <sub>AS</sub>		169	mJ
Single Pulsed Avalanche Current (Note 3)	I <sub>AS</sub>		2.6	Α
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55	to +150	°C





### 600V, 11A, $0.38\Omega$ N-Channel Power MOSFET

#### **Thermal Performance**

Dozomotov	Symbol	Limit		l lmi4
Parameter		ITO-220	IPAK/DPAK	Unit
Junction to Case Thermal Resistance	R <sub>eJC</sub>	3.8	1	°C/W
Junction to Ambient Thermal Resistance	R <sub>eJA</sub>		62	°C/W

Electrical Specifications (T<sub>.I=25°</sub>C unless otherwise noted)

Gate Threshold Voltage $V_{DS} = V_{GS}$ , $I_D = 250\mu A$ $V_{GS(TH)}$ 2           Gate Body Leakage $V_{GS} = \pm 30V$ , $V_{DS} = 0V$ $I_{GSS}$ ±1           Zero Gate Voltage Drain Current $V_{DS} = 600V$ , $V_{GS} = 0V$ $I_{DSS}$ ±1           Drain-Source On-State Resistance $V_{GS} = 10V$ , $I_D = 5.5A$ $R_{DS(ON)}$ 0.31         0.0           Dynamic (Note 5)           Total Gate Charge $V_{DS} = 380V$ , $I_D = 11A$ , $V_{GS} = 10V$ $V_{DS} = 380V$ , $V_{DS} = 10V$	- V 4 V 00 nA 1 μA 38 Ω
Gate Threshold Voltage $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$ $V_{GS(TH)}$ 2           Gate Body Leakage $V_{GS} = \pm 30V$ , $V_{DS} = 0V$ $I_{GSS}$ ±1           Zero Gate Voltage Drain Current $V_{DS} = 600V$ , $V_{GS} = 0V$ $I_{DSS}$ Drain-Source On-State Resistance $V_{GS} = 10V$ , $I_D = 5.5A$ $V_{DS} = 10V$	4 V 00 nA 1 μA 38 Ω
	00 nA I μA 38 Ω
Zero Gate Voltage Drain Current $V_{DS} = 600V$ , $V_{GS} = 0V$ $I_{DSS}$ Drain-Source On-State Resistance $V_{GS} = 10V$ , $I_{D} = 5.5A$ $R_{DS(ON)}$ 0.31         0.           Dynamic (Note 5)           Total Gate Charge $V_{DS} = 380V$ , $V_{DS} = 11A$ , $V_{GS} = 10V$ $V_{DS} = 380V$ , $V_{DS} = 11A$ , $V_{DS} = 10V$	1 μA 38 Ω
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	38 Ω
	-
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	- nC
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	
Output Capacitance $f = 1.0 MHz$ $C_{oss}$ 66  Gate Resistance $f = 1.0 MHz$ , open drain $R_g$ 3.2  Switching (Note 6)  Turn-On Delay Time $t_{d(on)}$ 24	-
Gate Resistance $f=1MHz$ , open drain $R_g$ 3.2  Switching (Note 6)  Turn-On Delay Time $t_{d(on)}$ 24	-
Switching (Note 6)  Turn-On Delay Time  t <sub>d(on)</sub> 24	- pF
Turn-On Delay Time t <sub>d(on)</sub> 24	- Ω
V - 290V	
Turn-On Rise Time $V_{DD} = 380V$ , $t_c = -28$	-
	-
Turn-Off Delay Time $R_{GEN} = 35\Omega, \\ I_D = 11A, V_{GS} = 10V, \\ t_{d(off)} \qquad \qquad 70$	ns -
T 0" F " T"	-
Source-Drain Diode (Note 4)	
Forward On Voltage $I_{S}=11A, V_{GS}=0V$ $V_{SD}$ 1	.4 V
Reverse Recovery Time $V_B=200V$ , $I_S=5.5A$ $t_{rr}$ 210	- ns
Develope Deservoir Charge	- μC

#### Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L=50mH,  $I_{AS}$ =2.6A,  $V_{DD}$ =50V,  $R_{G}$ =25 $\Omega$ , Starting  $T_{J}$ =25 $^{\circ}$ C
- 4. Pulse test: PW ≤ 300μs, duty cycle ≤ 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

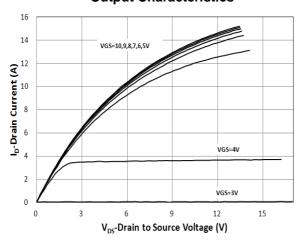


### 600V, 11A, $0.38\Omega$ N-Channel Power MOSFET

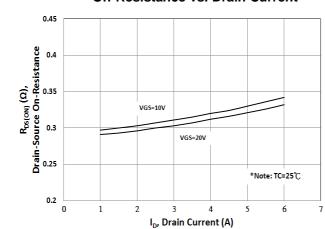


#### **Electrical Characteristics Curves**

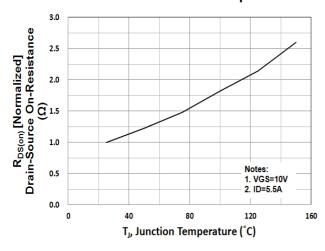
**Output Characteristics** 



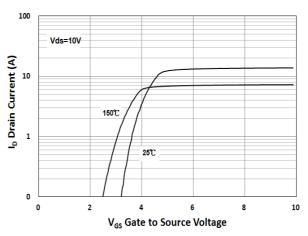
**On-Resistance vs. Drain Current** 



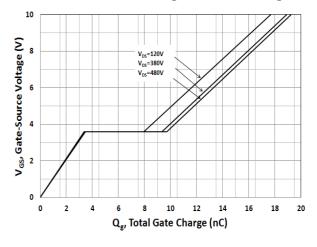
On-Resistance vs. Junction Temperature



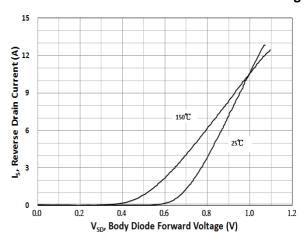
**Transfer Characteristics** 



Gate-Source Voltage vs. Gate Charge



Source-Drain Diode Forward Current vs. Voltage



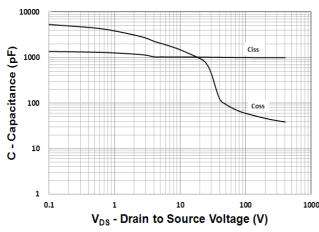


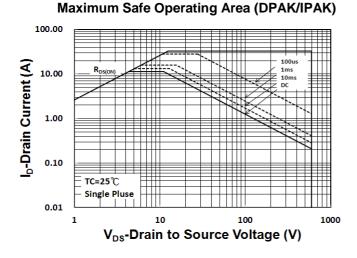
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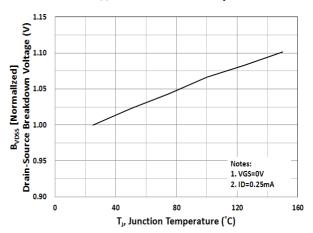
#### **Electrical Characteristics Curves**

Capacitance vs. Drain-Source Voltage

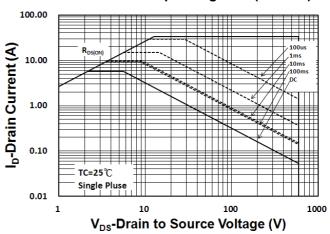




BV<sub>DSS</sub> vs. Junction Temperature



#### **Maximum Safe Operating Area (ITO-220)**



Version: A14

4/9

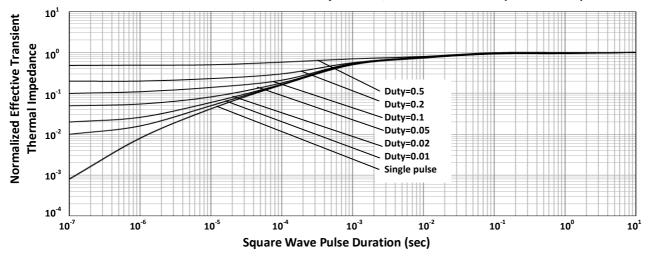


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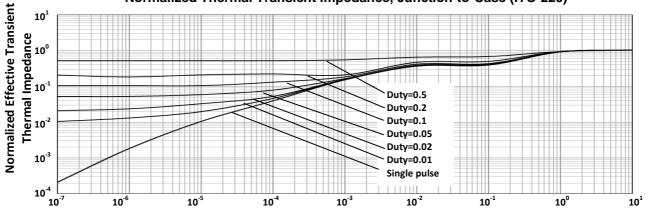


#### **Electrical Characteristics Curve**

#### Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)



#### Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)



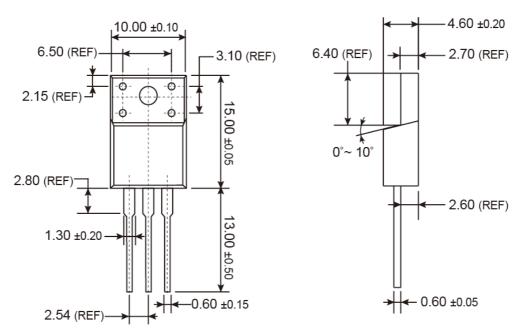
**Square Wave Pulse Duration (sec)** 



600V, 11A,  $0.38\Omega$  N-Channel Power MOSFET



### **ITO-220 Mechanical Drawing**



**Unit: Millimeters** 

### **Marking Diagram**



**G** = Halogen Free

Y = Year Code

**WW** = Week Code (01~52)

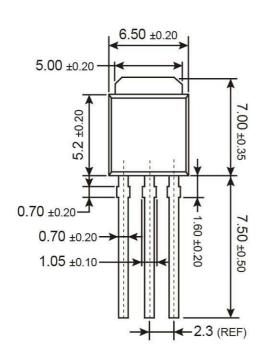
**F** = Factory Code

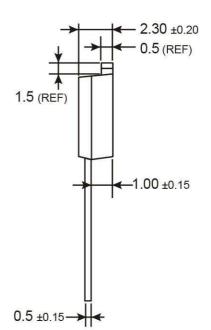


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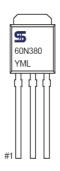
### **TO-251 (IPAK) Mechanical Drawing**





Unit: Millimeters

### **Marking Diagram**



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

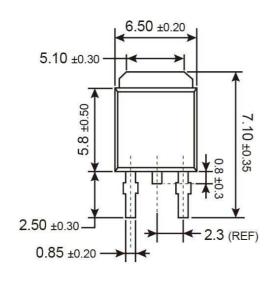
L = Lot Code

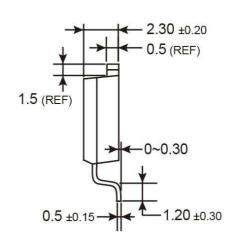


600V, 11A,  $0.38\Omega$  N-Channel Power MOSFET



### TO-252 (DPAK) Mechanical Drawing





Unit: Millimeters

### **Marking Diagram**



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code





600V, 11A,  $0.38\Omega$ N-Channel Power MOSFET

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